

IN THE CLAIMS:

- 1-16. (canceled)
17. (original) A precursor arrangement for manufacturing single-walled carbon nanotubes comprising:
- a substrate; and
- at least one pillar located on said substrate, said at least one pillar in turn comprising alternate layers of a first precursor material comprising fullerene molecules and a second precursor material comprising a catalyst.
18. (original) The precursor arrangement according to claim 17, wherein the layers have a thickness that decreases with their distance from the substrate.
19. (original) The precursor arrangement according to claim 17, wherein the substrate has at least one crystallization site for growing the single-walled carbon nanotubes.
20. (original) The precursor arrangement according to claim 19, wherein said substrate comprises at least one of molybdenum and thermally oxidized silicon, wherein said molybdenum is in the form of at least one of a grid and a solid film provided on a silicon wafer.
21. (original) The precursor arrangement according to claim 17, wherein the second precursor material comprises a magnetic material.
22. (original) The precursor arrangement according to claim 21, wherein the magnetic material is selected from the group consisting of Ni, Co, Fe, Mo.
23. (currently amended) A nanotube arrangement comprising:
- a substrate comprising at least one of molybdenum and thermally oxidized silicon; and

at least one crystal located on said substrate, said at least one crystal in turn comprising a bundle of single-walled carbon nanotubes with approximately identical orientation and structure.

24. (original) The nanotube arrangement according to claim 23, wherein the substrate has a surface with crystallization sites wherefrom the single-walled carbon nanotubes have grown.

25. (currently amended) The nanotube arrangement according to claim 24, ~~wherein the substrate comprises at least one of molybdenum and thermally oxidized silicon, and wherein said molybdenum is in the form of at least one of a~~ grid and a solid film provided on a silicon wafer.

26. (original) The nanotube arrangement according to claim 23 further comprising a plurality of said at least one crystals, wherein said plurality of said at least one crystals are substantially parallel to each other.

27. (original) The nanotube arrangement according to claim 23 wherein the single-walled carbon nanotubes are substantially straight along their length.

28. (currently amended) A nanotube crystal comprising a bundle of straight single-walled carbon nanotubes with approximately identical orientation and ~~structure~~diameter.

29. (currently amended) A display comprising:

at least one nanotube arrangement, said at least one nanotube arrangement in turn comprising:

a substrate comprising at least one of molybdenum and thermally oxidized silicon; and

at least one crystal located on said substrate, said at least one crystal in turn comprising a bundle of single-walled carbon nanotubes with approximately identical orientation and structure.

30. (currently amended) An electrical circuit comprising:

at least one nanotube arrangement, said at least one nanotube arrangement in turn comprising:

a substrate comprising at least one of molybdenum and thermally oxidized silicon; and

at least one crystal located on said substrate, said at least one crystal in turn comprising a bundle of single-walled carbon nanotubes with approximately identical orientation and structure.

31. (currently amended) A switching element comprising:

at least one nanotube arrangement, said at least one nanotube arrangement in turn comprising:

a substrate comprising at least one of molybdenum and thermally oxidized silicon; and

at least one crystal located on said substrate, said at least one crystal in turn comprising a bundle of single-walled carbon nanotubes with approximately identical orientation and structure.

32. (currently amended) A display comprising:

at least one nanotube crystal, said at least one nanotube crystal in turn comprising a bundle of straight single-walled carbon nanotubes with approximately identical orientation and ~~structure~~diameter.

33. (currently amended) An electrical circuit comprising:

at least one nanotube crystal, said at least one nanotube crystal in turn comprising a bundle of straight single-walled carbon nanotubes with approximately identical orientation and ~~structure~~diameter.

34. (currently amended) A switching element comprising:

at least one nanotube crystal, said at least one nanotube crystal in turn comprising a bundle of straight single-walled carbon nanotubes with approximately identical orientation and ~~structure~~diameter.